

描述 / Descriptions

DFN 2×2C-6L 塑封封装 N+N 沟道 MOS 场效应管。

Double N+N-CHANNEL MOSFET in a DFN 2×2C-6L Plastic Package.

特征 / Features

$V_{DS} (V) = 30V$

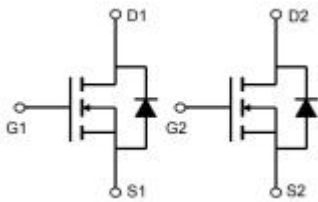
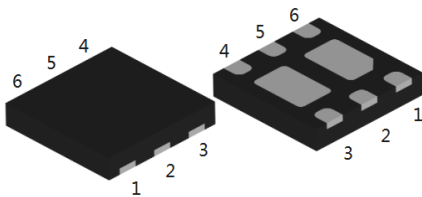
$I_D = 6.3A (V_{GS} = \pm 20V)$

无卤产品。HF Product.

用途 / Applications

电池保护开关，移动设备电池充放电，负载开关。

Battery protection switch, Mobile device battery charging and discharging, Load switch.

内部等效电路 / Equivalent Circuit**引脚排列 / Pinning**

出脚	定义
PIN 1	S1
PIN 2	G1
PIN 3	D2
PIN 4	S2
PIN 5	G2
PIN 6	D1

印章代码 / Marking

见印章说明 See Marking Instructions.

极限参数 / Absolute Maximum Ratings(Ta=25°C)

参数 Parameter	符号 Symbol	数值 Rating	单位 Unit
Drain-Source Voltage	V_{DSS}	30	V
Gate-Source Voltage	V_{GSS}	±20	V
Continuous Drain Current	$I_D (T_a=25^\circ\text{C})$	6.3	A
Pulsed Drain Current	I_{DM}	25	A
Power Dissipation for Single Operation	$P_D (T_a=25^\circ\text{C})$	2.8	W
Junction and Storage Temperature Range	T_J, T_{STG}	-55 to +150	°C
Maximum Junction-to-Ambient	$t \leq 10\text{s}$	$R_{\theta JA}$	44.6
	Steady-State	$R_{\theta JA}$	71.4

电性能参数 / Electrical Characteristics(Ta=25°C)

参数 Parameter	符号 Symbol	测试条件 Test Conditions	最小值 Min	典型值 Typ	最大值 Max	单位 Unit
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V$ $I_D=250\mu A$	30	35		V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=30V$ $V_{GS}=0V$			1.0	μA
Gate-Body leakage current	I_{GSS}	$V_{GS}=\pm 20V$ $V_{DS}=0V$			100	nA
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}$ $I_D=250\mu A$	1.0	1.7	2.5	V
Static Drain-Source On-Resistance	$R_{DS(on)}$	$V_{GS}=10V$ $I_D=9A$		20	22	mΩ
		$V_{GS}=4.5V$ $I_D=7A$		31	35	mΩ
Diode Forward Voltage	V_{SD}	$V_{GS}=0V$ $I_S=1.0A$			1.2	V
Input Capacitance	C_{iss}	$V_{DS}=25V$ $V_{GS}=0V$ $f=1.0\text{MHz}$		690		pF
Output Capacitance	C_{oss}			200		pF
Reverse Transfer Capacitance	C_{rss}			130		pF
Gate resistance	R_g	$V_{DS}=0V$ $V_{GS}=0V$ $f=1.0\text{MHz}$		2.7		Ω
Total Gate Charge(10V)	Q_g	$V_{GS}=10V$ $V_{DS}=15V$ $I_D=6A$		5.2		nC
Total Gate Charge(4.5V)				2.5		nC
Gate-Source Charge	Q_{gs}			0.8		nC
Gate-Drain Charge	Q_{gd}			1.3		nC
Turn-On Delay Time	$t_{d(on)}$	$V_{DS}=15V$ $V_{GS}=10V$ $R_L=2.5\Omega$ $R_{GEN}=3\Omega$		4.5		ns
Turn-On Rise Time	t_r			2.5		ns
Turn-Off Delay Time	$t_{d(off)}$			14.5		ns
Turn-Off Fall Time	t_f			3.5		ns

电参数曲线图 / Electrical Characteristic Curve

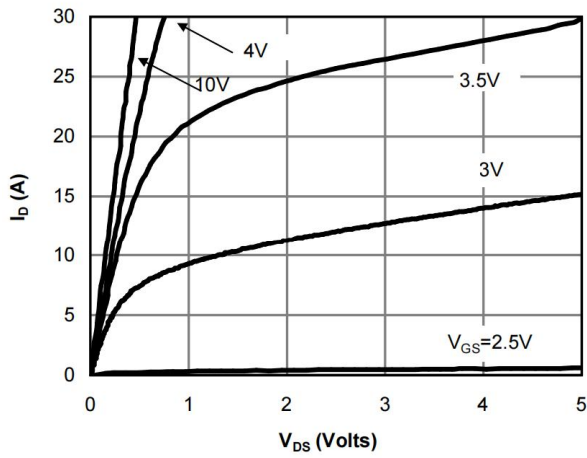


Fig 1: On-Region Characteristics

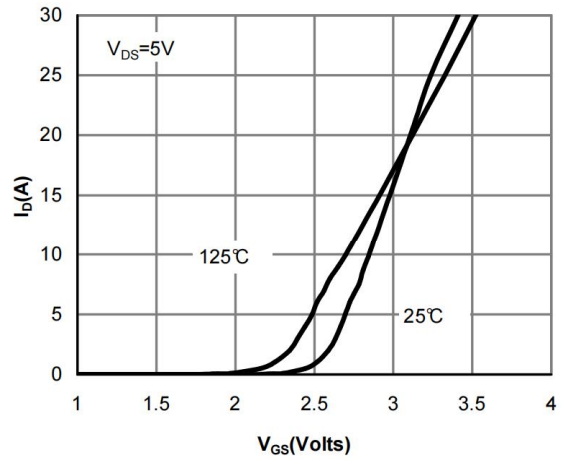


Figure 2: Transfer Characteristics

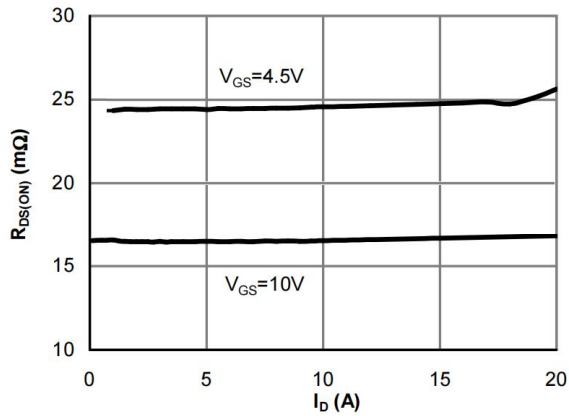


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

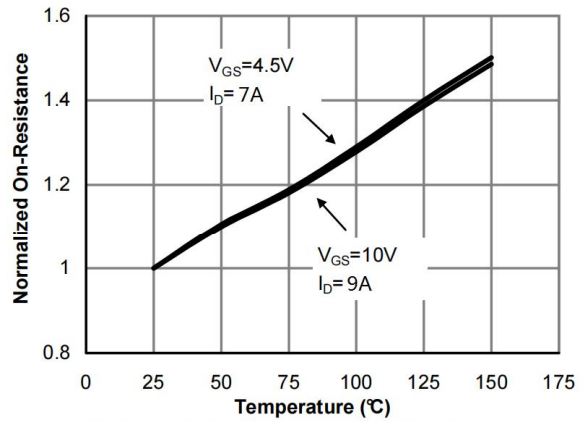


Figure 4: On-Resistance vs. Junction Temperature

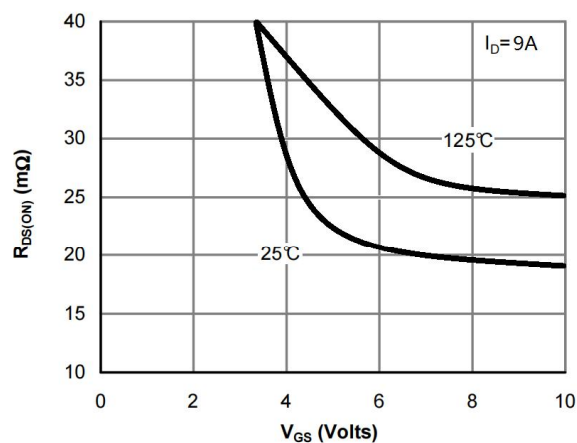


Figure 5: On-Resistance vs. Gate-Source Voltage

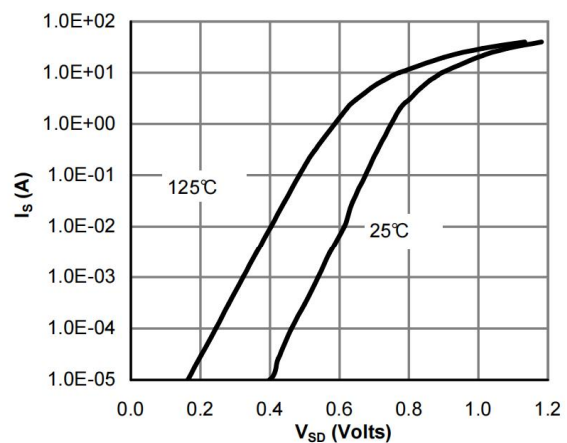


Figure 6: Body-Diode Characteristics

电参数曲线图 / Electrical Characteristic Curve

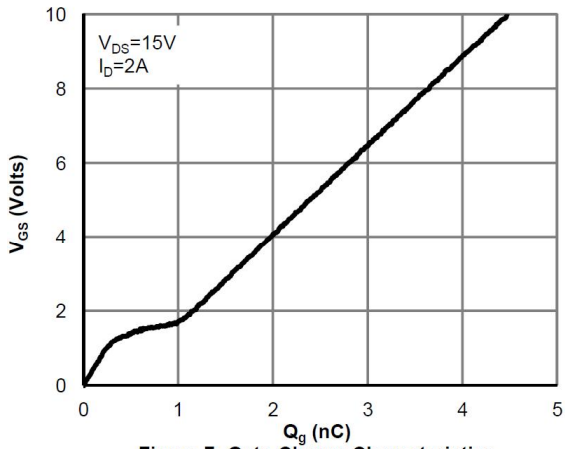


Figure 7: Gate-Charge Characteristics

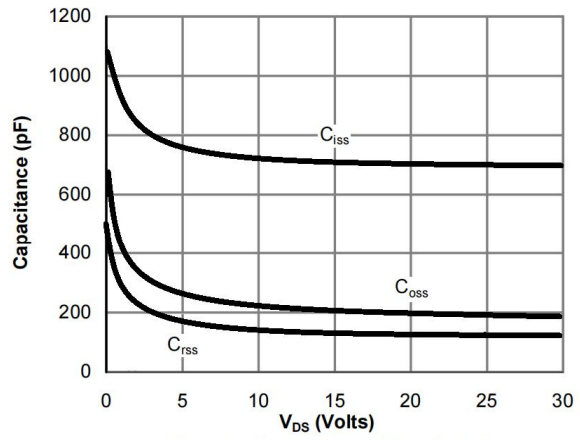


Figure 8: Capacitance Characteristics

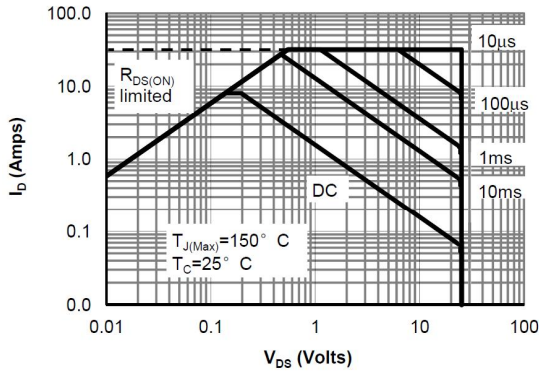


Figure 9: Maximum Forward Biased Safe Operating Area

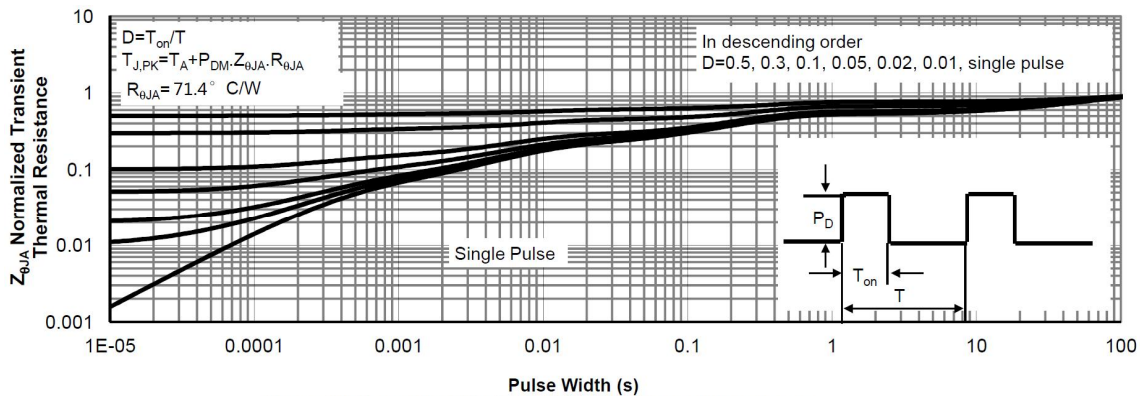
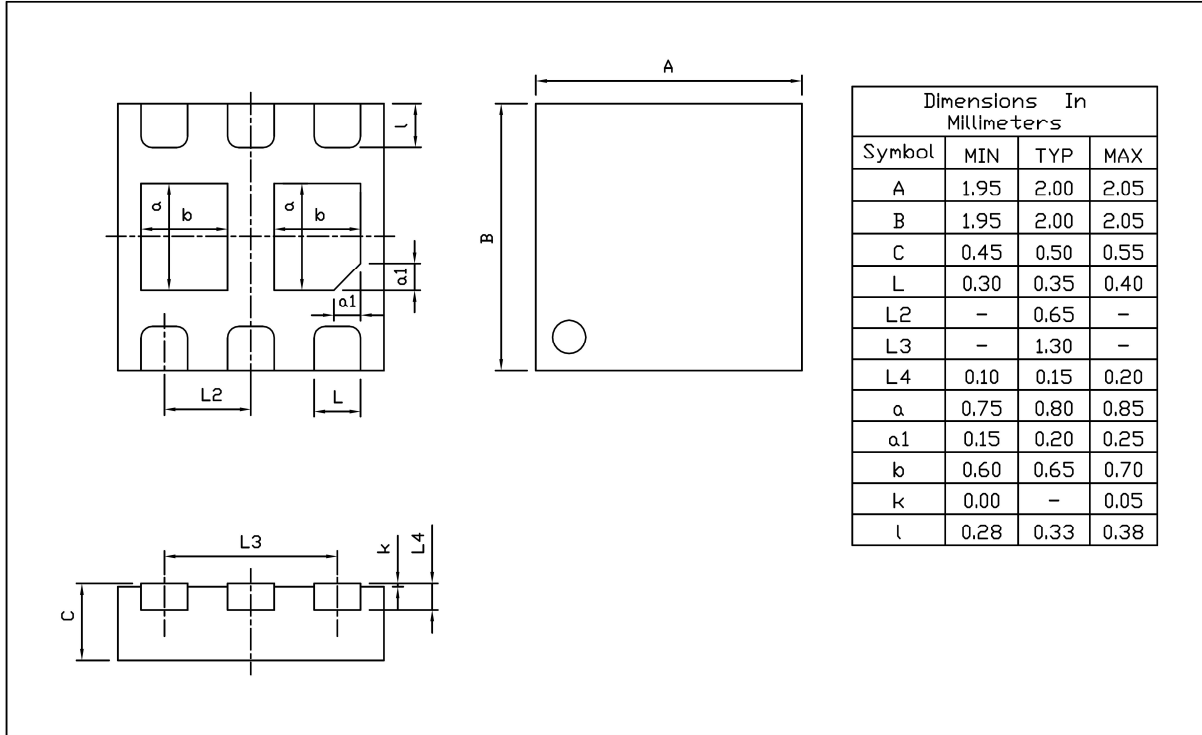


Figure 10: Normalized Maximum Transient Thermal Impedance

外形尺寸图 / Package Dimensions

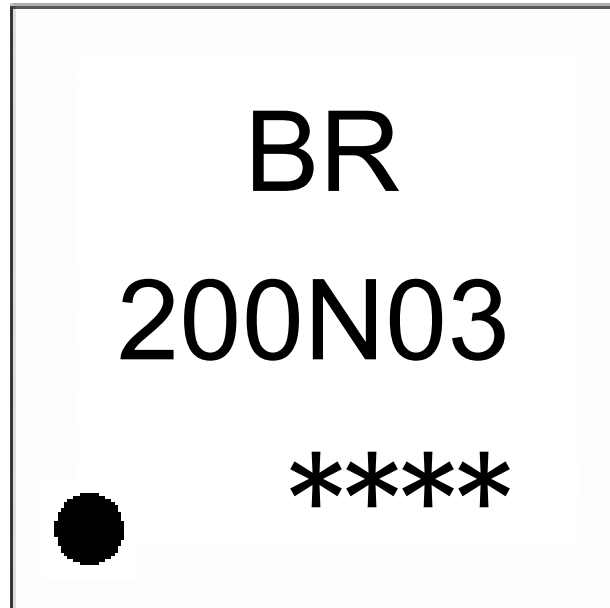
DFN2 × 2C-6L-0.5

Unit:mm



Rev.00 202204

印章说明 / Marking Instructions



说明：

BR： 为公司代码

200N03： 为型号代码

****： 为生产批号代码，随生产批号变化

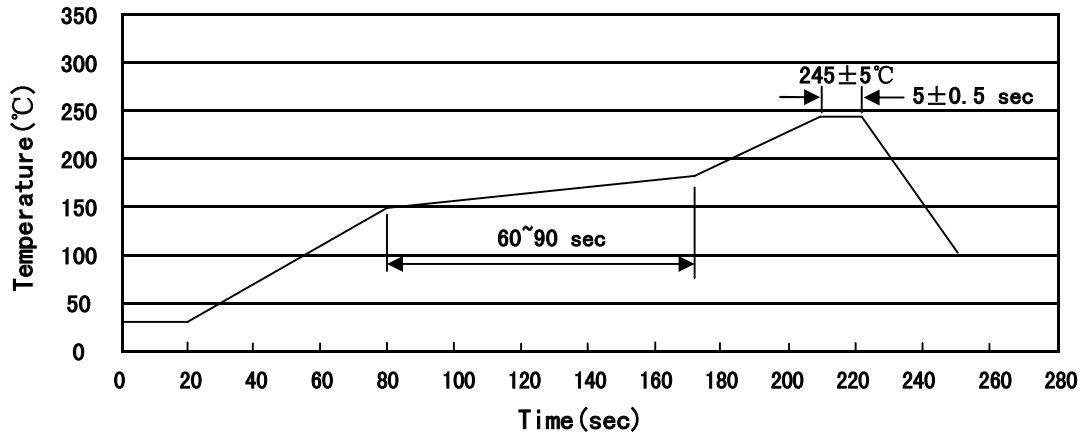
Note:

BR: Company Code

200N03: Product Type

****: Lot No. Code, code change with Lot No

回流焊温度曲线图(无铅) / Temperature Profile for IR Reflow Soldering(Pb-Free)



说明：

- 1、预热温度 150 ~ 180°C，时间 60 ~ 90sec;
- 2、峰值温度 245±5°C，时间持续为 5±0.5sec;
- 3、焊接制程冷却速度为 2 ~ 10°C/sec.

Note:

- 1.Preheating:150~180°C, Time:60~90sec.
- 2.Peak Temp.:245±5°C, Duration:5±0.5sec.
3. Cooling Speed: 2~10°C/sec.

耐焊接热试验条件 / Resistance to Soldering Heat Test Conditions

温度：260±5°C

时间：10±1 sec.

Temp.:260±5°C

Time:10±1 sec

包装规格 / Packaging SPEC.

卷盘包装 / REEL

Package Type 封装形式	Units 包装数量					Dimension 包装尺寸 (unit: mm ³)		
	Units/Reel 只/卷盘	Reels/Inner Box 卷盘/盒	Units/Inner Box 只/盒	Inner Boxes/Outer Box 盒/箱	Units/Outer Box 只/箱	Reel	Inner Box 盒	Outer Box 箱
DFN 2 × 2C-6L	4,000	10	40,000	4	160,000	7" × 8	210×205×205	445×230×435

使用说明 / Notices